



N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C		
30V	14mΩ @ V <sub>GS</sub> = 10V	8.6A		
307	20mΩ @ V <sub>GS</sub> = 4.5V	7.1A		

## Description

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

#### Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### Mechanical Data

Case: SO-8

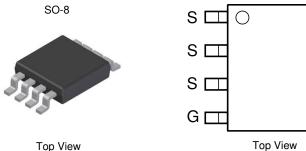
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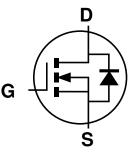
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- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072g (Approximate)



Internal Schematic



Equivalent Circuit

## Ordering Information (Note 5)

Part Number	Case	Packaging
DMN4800LSSQ-13	SO-8	2,500/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

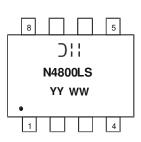
 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



Chile Hanufacturer's Marking
N4800LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 13 = 2013)
WW = Week (01 - 53)



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	30	V	
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Ducio Current (Nate 7) V 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	8.6 6.3	А
Continuous Drain Current (Note 7) $V_{GS} = 10V$	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	11.8 9.0	А
Maximum Body Diode Forward Current (Note 7)			I <sub>S</sub>	2.4	А
Pulsed Drain Current (Note 8)			IDM	50	А

### **Thermal Characteristics**

Characteristic	Symbol	Value	Units		
Tatal Bower Dissipation (Note 6)	$T_A = +25^{\circ}C$	Р	1.46	w	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	P <sub>D</sub>	0.9	vv	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	P	86	°C/W	
	t<10s	R <sub>0JA</sub>	46	0/10	
Total Power Dissipation (Note 7)	$T_A = +25^{\circ}C$	— P <sub>D</sub>	1.7	w	
Total Fower Dissipation (Note 7)	$T_A = +70^{\circ}C$	FD	1.0		
Thermal Resistance, Junction to Ambient (Note 7)	Steady state	Р	75		
mermai Resistance, sunction to Ambient (Note 7)	t<10s	− R <sub>θJA</sub>	40	°C/W	
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	15		
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	0°		

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

			-			<b>T</b> 10 100
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30		_	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		—	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.8	1.2	1.6	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
Static Drain-Source On-Resistance		11	11	14	mΩ	$V_{GS} = 10V, I_{D} = 9A$
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	14	20	11122	$V_{GS} = 4.5V, I_D = 7A$
Forward Transconductance	<b>g</b> <sub>fs</sub>	_	8		S	$V_{DS} = 10V, I_D = 9A$
Diode Forward Voltage	V <sub>SD</sub>	_	0.72	0.94	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	Ciss	_	798	_	pF	
Output Capacitance	Coss	_	128	_	pF	$-V_{DS} = 10V, V_{GS} = 0V$ -f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	122	_	pF	1 = 1.000112
Gate Resistance	R <sub>G</sub>	_	1.37	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge	Qg	_	8.7	_		
Gate-Source Charge	Q <sub>gs</sub>	_	1.7	_	nC	$V_{GS} = 5V, V_{DS} = 15V, I_D = 9A$
Gate-Drain Charge	Q <sub>gd</sub>	_	2.4	_		
Turn-On Delay Time	t <sub>d(on)</sub>	_	5.03			$\label{eq:VDD} \begin{split} V_{DD} &= 15V,  V_{GEN} = 10V, \\ R_L &= 15\Omega,  R_G = 6.0\Omega,  I_D = 1A \end{split}$
Rise Time	tr	_	4.50		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	_	26.33	_	115	
Fall Time	t <sub>f</sub>	_	8.55	_		

6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.

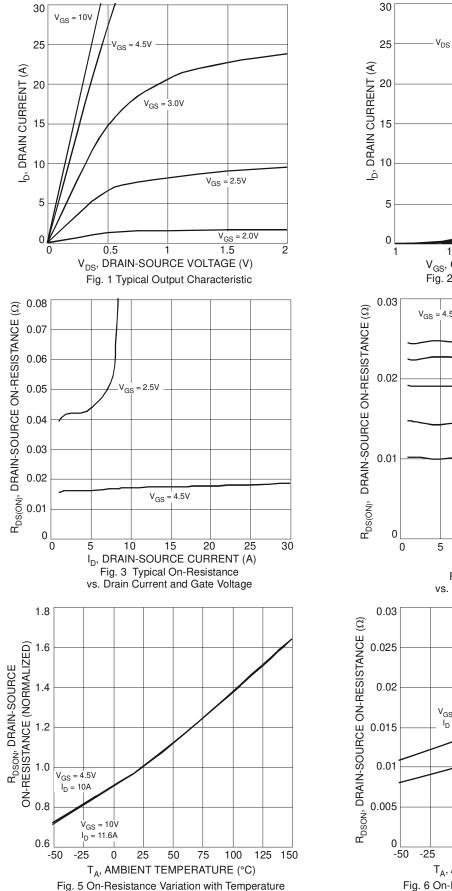
8. Repetitive rating, pulse width limited by junction temperature.

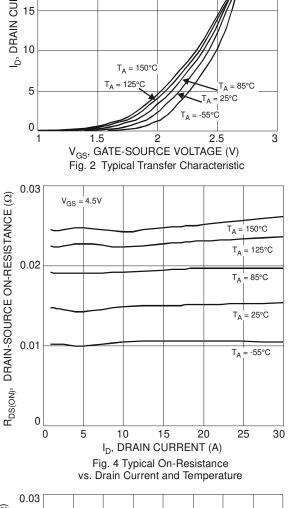
Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

Notes:

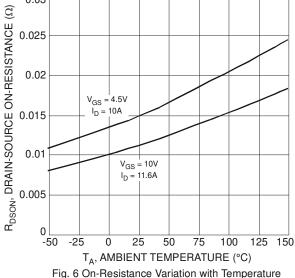


# DMN4800LSSQ



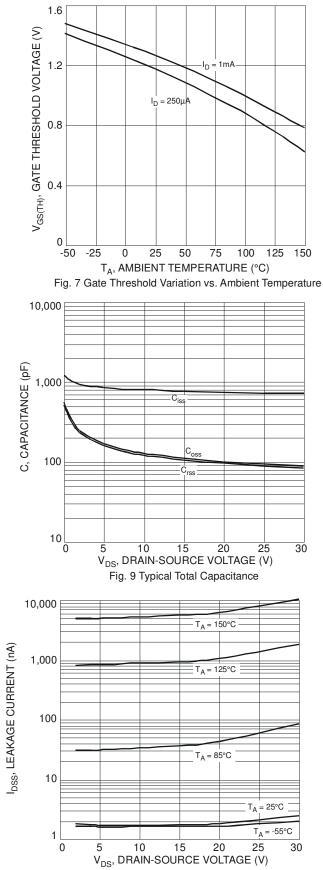


5V

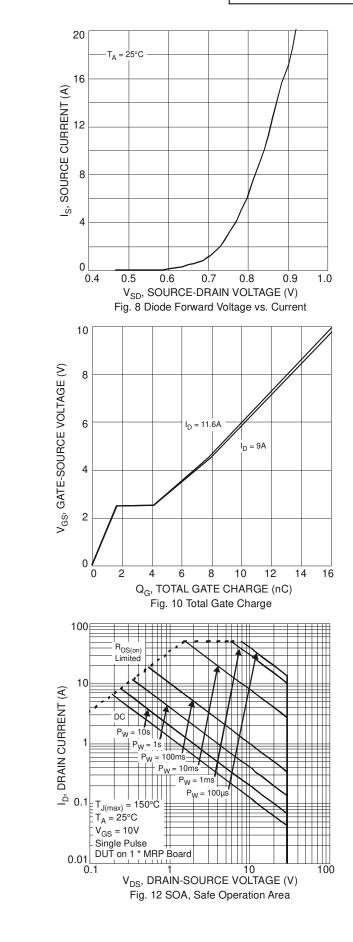




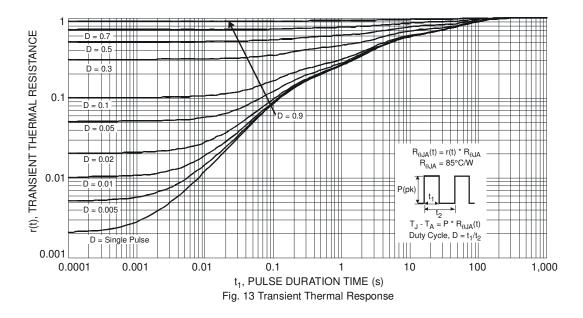
# DMN4800LSSQ





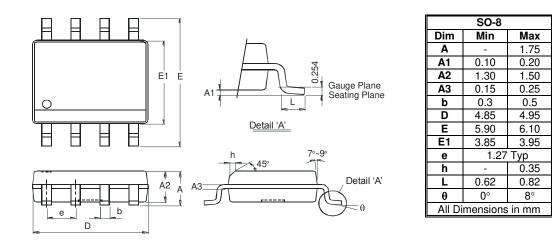






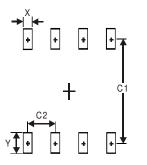
## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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